

DMN21D2UFB-7B Datasheet



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DiGi Electronics Part Number DMN21D2UFB-7B-DG

Manufacturer Diodes Incorporated

Manufacturer Product Number DMN21D2UFB-7B

Description MOSFET N-CH 20V 760MA 3DFN

Detailed Description N-Channel 20 V 760mA (Ta) 380mW (Ta) Surface M

ount X1-DFN1006-3



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
DMN21D2UFB-7B	Diodes Incorporated
Series:	Product Status:
	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
20 V	760mA (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
1.5V, 4.5V	990m0hm @ 100mA, 4.5V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
1V @ 250μA	0.93 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±12V	27.6 pF @ 16 V
FET Feature:	Power Dissipation (Max):
	380mW (Ta)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
X1-DFN1006-3	3-UFDFN
Base Product Number:	
DMN21	

Environmental & Export classification

8541.21.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	





20V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
	0.99Ω @ V _{GS} = 4.5V	760mA
20V —	1.2Ω @ V _{GS} = 2.5V	700mA
	2.4Ω @ V _{GS} = 1.8V	500mA
	3.0Ω @ V _{GS} = 1.5V	350mA

Description and Applications

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

Features and Benefits

- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.0V Max
- Low Input Capacitance
- · Fast Switching Speed
- Ultra-Small Surface Mount Package 1mm x 0.6mm
- Low Package Profile, 0.5mm Maximum Package Height
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotive-products/.

 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.001 grams (Approximate)

X1-DFN1006-3

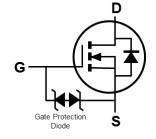








Top View Pin Configuration



Equivalent Circuit

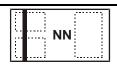
Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Tape Pitch (mm)	Quantity per Reel
DMN21D2UFB-7	NN	7	8	4	3,000
DMN21D2UFB-7B	NN	7	8	2	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



NN = Product Type Marking Code



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			VDSS	20	V
Gate-Source Voltage			V_{GSS}	±12	V
Continuous Drain Current (Note 6) V _{GS} = 4.5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	lo	760 610	mA
Continuous Drain Current (Note 6) VGS = 4.5V	t<5s	$T_A = +25$ °C $T_A = +70$ °C	lo	850 700	mA
Maximum Continuous Body Diode Forward Current (Note 6)			Is	0.8	Α
Pulsed Drain Current (Note 7)		IDM	1.0	Α	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)	$T_A = +25$ °C	PD	0.38	W	
Total Fower Dissipation (Note 3)	$T_A = +70$ °C	FD	0.25		
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	RеJA	325	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<5s	Көја	244	C/VV	
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	Po	0.9	W	
Total Fower Dissipation (Note o)	$T_A = +70$ °C	FU	0.57		
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	р	141	°C/W	
Thermal Resistance, Junction to Ambient (Note o)	t<5s	$R_{\theta JA}$	106	C/VV	
Operating and Storage Temperature Range	-	TJ, TSTG	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

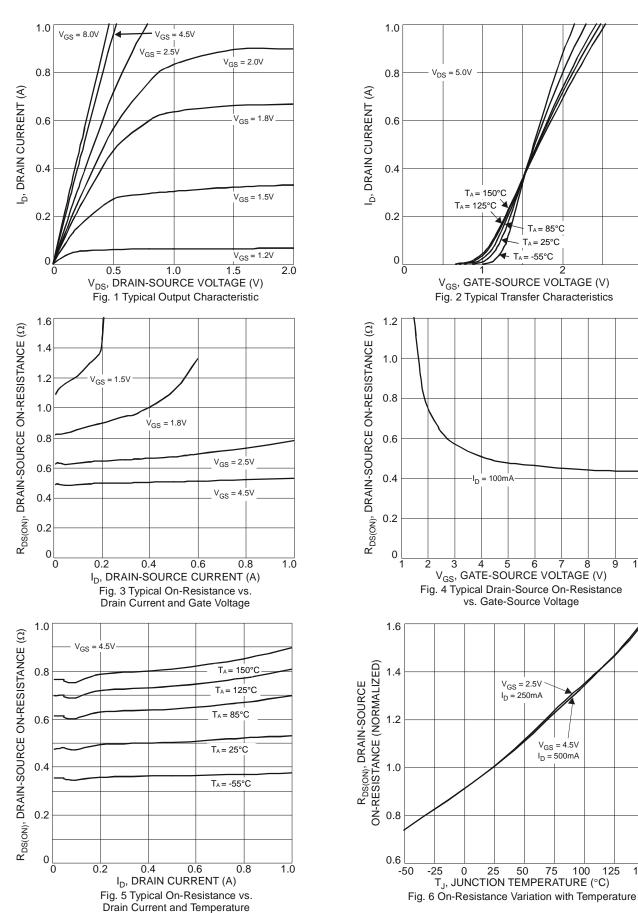
Characteristic	Symbo	I Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current @Tc = +:	25°C IDSS	_	_	100	nA	V _{DS} = 20V, V _{GS} = 0V	
Gate-Source Leakage	Igss	_	_	±1	μA	$V_{GS} = \pm 10V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	Vgs(TH	0.4	_	1.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
		_	0.6	0.99		$V_{GS} = 4.5V, I_D = 100mA$	
Static Drain-Source On-Resistance	D	_	0.7	1.2	Ω	$V_{GS} = 2.5V, I_{D} = 50mA$	
Static Drain-Source On-Resistance	RDS(ON	_	0.9	2.4	52	$V_{GS} = 1.8V, I_{D} = 20mA$	
			1.2	3.0		V _G S = 1.5V, I _D = 10mA	
Forward Transfer Admittance	Y _{fs}	180	_	_	ms	V _{DS} = 10V, I _D = 400mA	
Diode Forward Voltage	V _{SD}	_	0.6	1.0	V	$V_{GS} = 0V, I_{S} = 150mA$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	_	27.6	_	pF	101/1/ 01/	
Output Capacitance	Coss		4.0	_	pF	V _{DS} = 16V, V _{GS} = 0V, -f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	2.8	_	pF	1 = 1.01/11/12	
Total Gate Charge, VGS = 4.5V	Qg	_	0.41	_	nC		
Total Gate Charge, Vgs = 10V	Qg	_	0.93	_	nC	\/ 40\/ I- 250m A	
Gate-Source Charge	Q _{gs}	_	0.06	_	nC	$V_{DS} = 10V, I_{D} = 250mA$	
Gate-Drain Charge	Q_{gd}	_	0.06	_	nC	1	
Turn-On Delay Time	t _D (ON)	_	3.5	_	ns	101/11/	
Turn-On Rise Time		_	4.2	_	ns	V _{DD} = 10V, V _{GS} = 4.5V,	
Turn-Off Delay Time	tD(OFF)	_	19.6	_	ns	$R_L = 47\Omega$, $R_g = 10\Omega$,	
Turn-Off Fall Time	tf	_	9.8	_	ns	I _D = 200mA	

Notes:

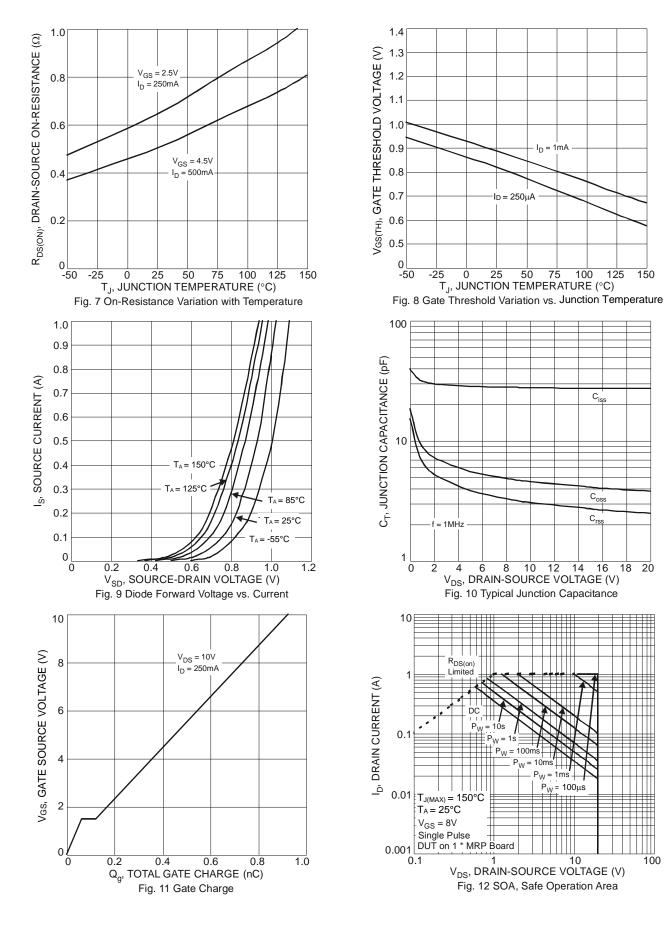
- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
- 7. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.



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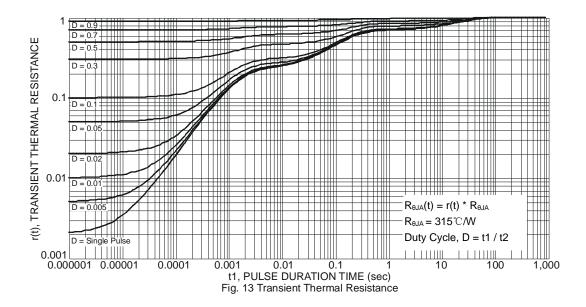






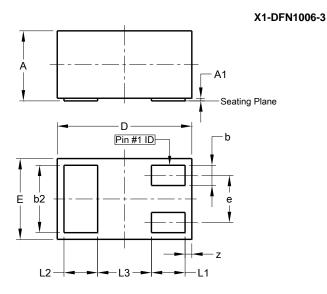
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Package Outline Dimensions

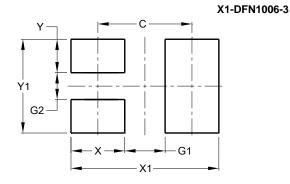
Please see http://www.diodes.com/package-outlines.html for the latest version.



Х	X1-DFN1006-3					
Dim	Min	Max	Тур			
Α	0.47	0.53	0.50			
A1	0.00	0.05	0.03			
b	0.10	0.20	0.15			
b2	0.45	0.55	0.50			
D	0.95	1.075	1.00			
E	0.55	0.675	0.60			
е	-	-	0.35			
L1	0.20	0.30	0.25			
L2	0.20	0.30	0.25			
L3	-	-	0.40			
Z	0.02	0.08	0.05			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
Х	0.40
X1	1.10
Y	0.25
Y1	0.70



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